BC817-40W

45 V, 0.5 A, General Purpose NPN Transistor

ON Semiconductor's BC817–40W is a General Purpose NPN Transistor that is housed in the SC–70/SOT–323 package.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This Device is Pb–Free, Halogen Free/BFR Free and is RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	45	V
Collector – Base Voltage	V _{CBO}	50	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	Ic	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1)	P _D	460	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

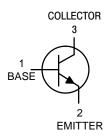
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm²



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SC-70 CASE 419 STYLE 3

MARKING DIAGRAM



CE = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION[†]

Device	Package	Shipping
BC817-40WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NSVBC817-40WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

BC817-40W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(VR)CEO}	45	_	_	V	
Collector – Emitter Breakdown Voltage (V _{EB} = 0 V, I _C = 10 μA)	V _{(VR)CES}	50	_	-	V	
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	V _{(VR)EBO}	5.0	_	-	V	
Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}		_ _	100 5.0	nA μA	
ON CHARACTERISTICS						
DC Current Gain (Note 2) $(I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V})$ $(I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V})$	h _{FE}	250 40		600 -	-	
Collector – Emitter Saturation Voltage (Note 2) $(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$	V _{CE(sat)}	-	_	0.7	V	
Base – Emitter On Voltage (Note 2) ($I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$)	V _{BE(on)}	-	_	1.2	V	
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T	100	_	-	MHz	
Output Capacitance $(V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz})$	C _{obo}	-	10	-	pF	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Condition: Pulse Width = 300 μ sec, Duty Cycle \leq 2%

BC817-40W

TYPICAL CHARACTERISTICS

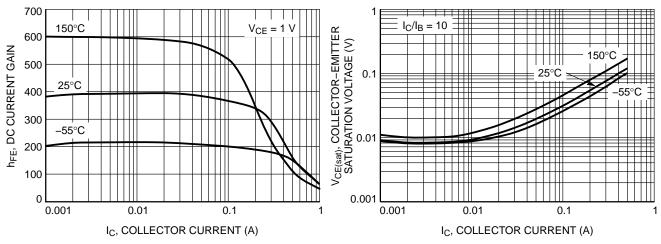


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

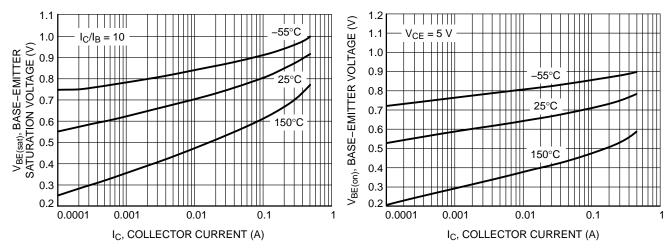


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

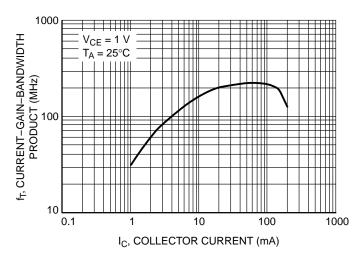
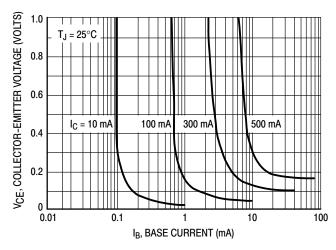


Figure 5. Current Gain Bandwidth Product vs.
Collector Current

TYPICAL CHARACTERISTICS



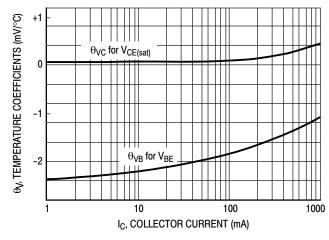


Figure 6. Saturation Region

Figure 7. Temperature Coefficients

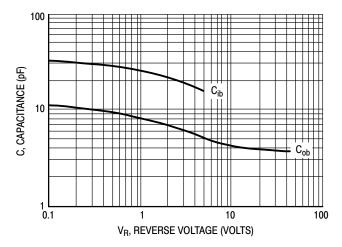


Figure 8. Capacitances

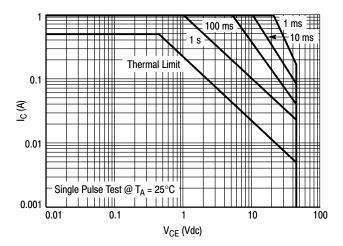


Figure 9. Safe Operating Area





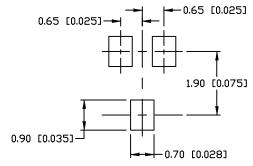
SC-70 (SOT-323) CASE 419 ISSUE P

DATE 07 OCT 2021

NOTES:

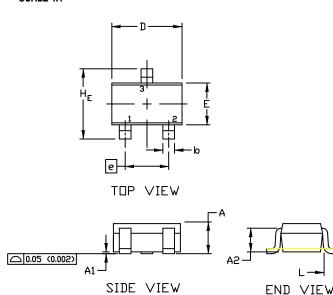
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
Ε	1.15	1.24	1.35	0.045	0.049	0.053	
e	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC				0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	
				`			



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G

NSVDTC143ZM3T5G SMUN5335DW1T2G SMUN5216DW1T1G NSVMUN5312DW1T2G